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TITLE: Non-volatile memory device and
method for manufacturing
the same

INVENTOR: RA, G Y

PRIORITY-DATA: 1999KR-0043852 (October 11, 1999)

PATENT-FAMILY:

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ABSTRACTED-PUB-NO: KR2001036727A

BASIC-ABSTRACT:

NOVELTY - A non-volatile memory device and a method for manufacturing the same are provided to improve the program efficiency of a memory device by generating thermoelectrons from a source region.

DETAILED DESCRIPTION - A gate insulating layer(22) is formed on a substrate(21). A floating gate(23) is formed on the gate insulating layer(22). A conductive sidewall(25) is formed at one side of the floating gate(23). An ONO(Oxide-Nitride-Oxide) layer(29) is formed on a whole face of the substrate(21) including the conductive sidewall(25) and the floating gate(23). A control gate(30) is formed on the ONO layer(29). A source region(26) is

formed on a surface of the substrate(21) of the conductive sidewall(25). A drain region(27) is formed on a surface of the substrate(21) corresponding to the source region(26).

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Basic Abstract Text - ABTX (2):

DETAILED DESCRIPTION - A gate insulating layer(22) is formed on a substrate(21). A floating gate(23) is formed on the gate insulating layer(22). A conductive sidewall(25) is formed at one side of the floating gate(23). An . ONO(Oxide-Nitride-Oxide) layer(29) is formed on a whole face of the substrate(21) including the conductive sidewall(25) and the floating gate(23). A control gate(30) is formed on the ONO layer(29). A source region(26) is formed on a surface of the substrate(21) of the conductive sidewall(25). A drain region(27) is formed on a surface of the substrate(21) corresponding to the source region(26).

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